

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	1	chuang near keun.in.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 19:43	
2	BRS	L2	1	wey near shane-shyan.in.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 19:43	
3	BRS	L3	18	jou near ming-jiunn.in.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 19:45	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	0	sung near shu-weng.in.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/08/01 19:45	
5	BRS	L5	5	sung near shu-wen.in.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/08/01 19:45	
6	BRS	L6	6	liu near chia-cheng.in.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/08/01 19:46	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L7	9	huang near chao-nien.in.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 19:46	
8	BRS	L8	1029	438/22.ccls.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 19:56	
9	BRS	L9	62477	(transparent) near (wafer or substrate)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 19:56	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	497	(transparent) near (wafer or substrate) near15 (amorphous near3 layer)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 19:58	
11	BRS	L11	2	(transparent) near (wafer or substrate) near15 (amorphous near3 layer) near25 (ohmic near3 electrode)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 19:58	
12	BRS	L12	223	(transparent) near (wafer or substrate) near15 (amorphous near3 layer) near25 (electrode)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 20:12	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	2480	(wafer or substrate) near15 (amorphous near3 layer) near25 (electrode)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 20:12	
14	BRS	L14	6	(wafer or substrate) near15 (amorphous near3 layer) near25 (quantum near well or mqw)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 20:13	
15	BRS	L15	3585	(wafer or substrate) near15 (amorphous near3 layer) near25 (multiple near quantum near well) or (mqw)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 20:14	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
16	BRS	L16	2	(wafer or substrate) near15 (amorphous near3 layer) near25 ((multiple near quantum near well) or (mqw))	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 20:14	
17	BRS	L17	1	(wafer or substrate) near15 (amorphous near3 layer) near25 ((multiple near quantum near well) or (mqw)) near15 (p-type near3 layer)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 20:15	
18	BRS	L18	0	(wafer or substrate) near15 (amorphous near3 layer) near25 ((multiple near quantum near well) or (mqw)) near15 (cladding near layer)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 20:15	

	U	1	Document ID	Title	Current OR	Pages
1	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20040094756 A1	METHOD FOR FABRICATING LIGHT-EMITTING DIODE USING NANOSIZE NITRIDE SEMICONDUCTOR MULTIPLE QUANTUM WELLS	257/13	14
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20020070841 A1	Semiconductor piezoresistor	338/5	8
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6441716 B1	Semiconductor piezoresistor	338/2	8
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6275137 B1	Semiconductor piezoresistor	338/2	8
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6103543 A	Fabrication of device electrodes in gan and related materials	438/46	20
6	<input type="checkbox"/>	<input type="checkbox"/>	US 5051786 A	Passivated polycrystalline semiconductors quantum well/superlattice structures fabricated thereof	257/22	11